

ABSTRACT OF THE DISCLOSURE

A method of forming a flash memory cell includes providing a substrate, forming an oxide layer over the substrate, forming a polysilicon floating gate over the oxide layer including providing a bottom seed layer having microcrystalline polysilicon, providing an upper amorphous silicon layer over the bottom seed layer, and annealing the upper amorphous silicon layer, providing an inter-poly dielectric layer over the floating gate, and forming a polysilicon control gate over the inter-poly dielectric layer.

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